



Semiconductor light emitting device especially LED

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Inventor: NAKATSU HIROSHI (JP)
Applicant: SHARP KK (JP)
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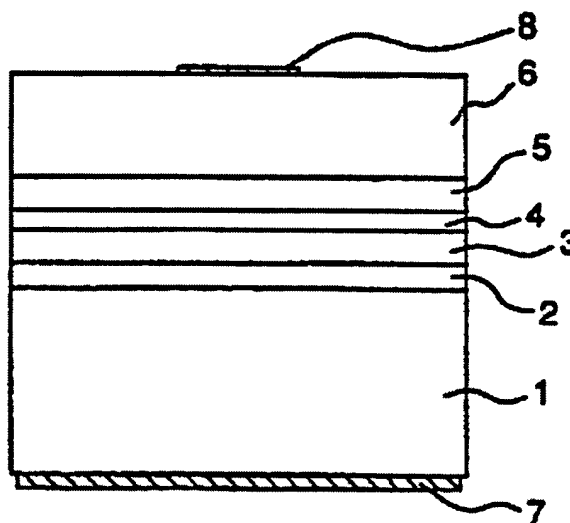
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Abstract of DE19756856

In a semiconductor light emitting device having a light emission layer (4) which is formed on and lattice matched with a semiconductor substrate (1) and which emits light of a wavelength not absorbed by the substrate, the basic semiconductor material of the light emission layer (4) is doped with one or more impurities acting as radiation recombination centres. Preferably, the light emission layer consists of an AlGaInP material, preferably $(\text{Al}_x\text{Ga}_{1-x})_1\text{In}_y\text{P}$, which is doped with a donor level-forming impurity (N, O, Se, S or Te) and an acceptor level-forming impurity (Mg, Zn or Cd).



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